

June 2010

FDD86326

N-Channel PowerTrench[®] MOSFET 80 V, 37 A, 23 m Ω

Features

- Max $r_{DS(on)}$ = 23 m Ω at V_{GS} = 10 V, I_D = 8 A
- Max $r_{DS(on)}$ = 37 m Ω at V_{GS} = 6 V, I_D = 4.6 A
- High performance trench technology for extremely low r_{DS(on)}
- High power and current handling capability in a widely used surface mount package
- Very low Qg and Qgd compared to competing trench technologies
- Fast switching speed
- 100% UIL tested
- RoHS Compliant

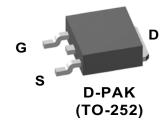


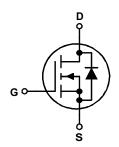
General Description

This N-Channel MOSFET is produced using Fairchild Semiconductor's advanced Power Trench® process that has been optimized for $r_{DS(on)}$, switching performance and ruggedness.

Applications

■ DC - DC Conversion





MOSFET Maximum Ratings $T_C = 25$ °C unless otherwise noted

| Symbol | Parameter | Ratings | Units | | |
|-----------------------------------|--|------------------------|-----------|-------------|-----|
| V_{DS} | Drain to Source Voltage | | | 80 | V |
| V_{GS} | Gate to Source Voltage | | | ±20 | V |
| | Drain Current -Continuous (Package limited) | T _C = 25 °C | | 42 | |
| I _D | -Continuous (Silicon limited) | T _C = 25 °C | | 37 | |
| | -Continuous | T _A = 25 °C | (Note 1a) | 8 | - A |
| | -Pulsed | | | 40 | |
| E _{AS} | Single Pulse Avalanche Energy | | (Note 3) | 121 | mJ |
| В | Power Dissipation | T _C = 25 °C | | 62 | w |
| P _D | Power Dissipation | T _A = 25 °C | (Note 1a) | 3.1 | |
| T _J , T _{STG} | Operating and Storage Junction Temperature Range | | | -55 to +150 | °C |

Thermal Characteristics

| $R_{	heta JC}$ | Thermal Resistance, Junction to Case | 2.0 | °C/W |
|-----------------|---|-----|------|
| $R_{\theta JA}$ | Thermal Resistance, Junction to Ambient (Note 1a) | 40 | C/VV |

Package Marking and Ordering Information

| Device Marking | Device | Package | Reel Size | Tape Width | Quantity |
|----------------|----------|---------------|-----------|------------|------------|
| FDD86326 | FDD86326 | D-PAK(TO-252) | 13 " | 12 mm | 2500 units |

Electrical Characteristics T_J = 25 °C unless otherwise noted

| Symbol | Parameter | Test Conditions | Min | Тур | Max | Units |
|--|---|--|-----|-----|------|-------|
| Off Chara | cteristics | | | | | |
| BV _{DSS} | Drain to Source Breakdown Voltage | $I_D = 250 \mu A, V_{GS} = 0 V$ | 80 | | | V |
| $\frac{\Delta BV_{DSS}}{\Delta T_{J}}$ | Breakdown Voltage Temperature Coefficient | I _D = 250 μA, referenced to 25 °C | | 67 | | mV/°C |
| I _{DSS} | Zero Gate Voltage Drain Current | V _{DS} = 64 V, V _{GS} = 0 V | | | 1 | μА |
| I _{GSS} | Gate to Source Leakage Current | V _{GS} = ±20 V, V _{DS} = 0 V | | | ±100 | nA |

On Characteristics (Note 2)

| V _{GS(th)} | Gate to Source Threshold Voltage | $V_{GS} = V_{DS}, I_{D} = 250 \mu A$ | 2 | 3.1 | 4 | V |
|--|--|---|---|------|----|-------|
| $\frac{\Delta V_{GS(th)}}{\Delta T_J}$ | Gate to Source Threshold Voltage Temperature Coefficient | I _D = 250 μA, referenced to 25 °C | | -8.5 | | mV/°C |
| | | V _{GS} = 10 V, I _D = 8 A | | 19 | 23 | |
| r _{DS(on)} | Static Drain to Source On Resistance | $V_{GS} = 6 \text{ V}, I_D = 4.6 \text{ A}$ | | 26 | 37 | mΩ |
| | | V _{GS} = 10 V, I _D = 8 A, T _J = 125 °C | | 33 | 44 | |
| 9 _{FS} | Forward Transconductance | V _{DS} = 10 V, I _D = 8 A | | 21 | | S |

Dynamic Characteristics

| C _{iss} | Input Capacitance | V - 50 V V - 0 V | 780 | 1035 | pF |
|------------------|------------------------------|---|-----|------|----|
| C _{oss} | Output Capacitance | V _{DS} = 50 V, V _{GS} = 0 V, f = 1 MHz | 180 | 240 | pF |
| C _{rss} | Reverse Transfer Capacitance | 1 - 1 101112 | 15 | 25 | pF |
| R_{g} | Gate Resistance | | 0.4 | | Ω |

Switching Characteristics

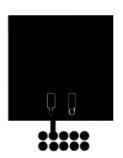
| t _{d(on)} | Turn-On Delay Time | | 7.6 | 15 | ns |
|---------------------|-------------------------------|--|------|----|----|
| t _r | Rise Time | V _{DD} = 50 V, I _D = 8 A, | 3.0 | 10 | ns |
| t _{d(off)} | Turn-Off Delay Time | V_{GS} = 10 V, R_{GEN} = 6 Ω | 13.4 | 24 | ns |
| t _f | Fall Time | | 2.9 | 10 | ns |
| Q_g | Total Gate Charge | V _{GS} = 0 V to 10 V | 13.4 | 19 | nC |
| Qg | Total Gate Charge | $V_{GS} = 0 \text{ V to 5 V}$ $V_{DD} = 50 \text{ V},$ | 7.6 | 11 | nC |
| Q_{gs} | Gate to Source Gate Charge | I _D = 8 A | 4.0 | | nC |
| Q _{gd} | Gate to Drain "Miller" Charge | | 3.7 | | nC |

Drain-Source Diode Characteristics

| Vob Source to Drain Dioge Forward Voltage | Source to Drain Diode, Ferward Voltage | $V_{GS} = 0 \text{ V}, I_{S} = 8 \text{ A}$ (Note 2) | | 0.8 | 1.3 | V |
|---|--|--|-----|-----|-----|----|
| | $V_{GS} = 0 \text{ V}, I_S = 2.6 \text{ A}$ (Note 2) | | 0.7 | 1.2 | V | |
| t _{rr} | Reverse Recovery Time | - I _F = 8 A, di/dt = 100 A/μs | | 43 | 68 | ns |
| Q _{rr} | Reverse Recovery Charge | | | 43 | 68 | nC |

Notes:

In R_{BJA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R_{BJC} is guaranteed by design while R_{BJA} is determined by the user's board design.



a. 40 °C/W when mounted on a 1 in² pad of 2 oz copper.



 b. 96 °C/W when mounted on a minimum pad of 2 oz copper.

- 2. Pulse Test: Pulse Width < 300 $\mu\text{s},$ Duty cycle < 2.0%.
- 3. Starting T_J = 25°C, L = 3 mH, I_{AS} = 9 A, V_{DD} = 80 V, V_{GS} = 10 V.

Typical Characteristics T_J = 25 °C unless otherwise noted

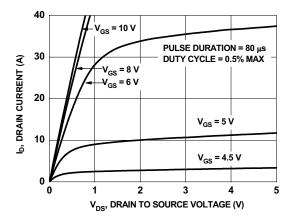


Figure 1. On-Region Characteristics

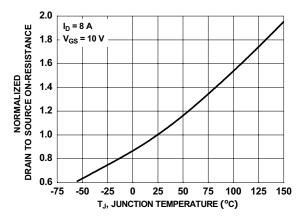


Figure 3. Normalized On-Resistance vs Junction Temperature

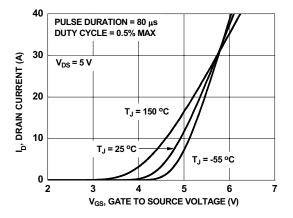


Figure 5. Transfer Characteristics

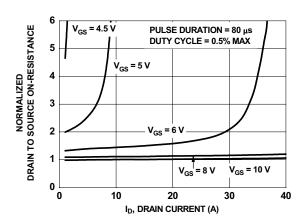


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

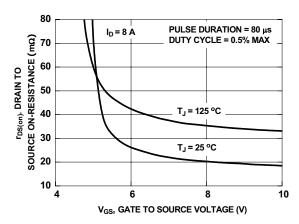


Figure 4. On-Resistance vs Gate to Source Voltage

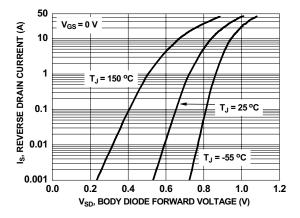


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

Typical Characteristics $T_J = 25$ °C unless otherwise noted

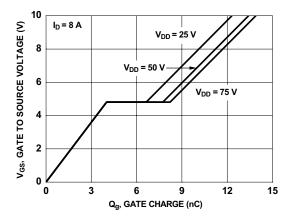


Figure 7. Gate Charge Characteristics

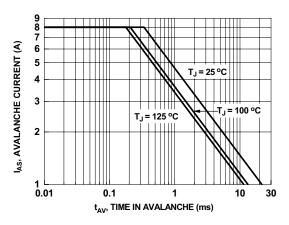


Figure 9. Unclamped Inductive Switching Capability

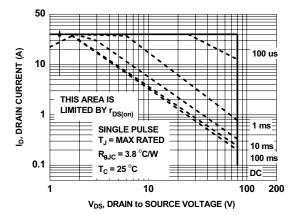


Figure 11. Forward Bias Safe Operating Area

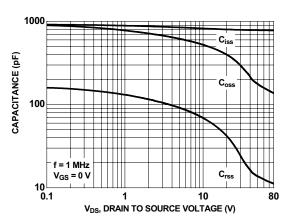


Figure 8. Capacitance vs Drain to Source Voltage

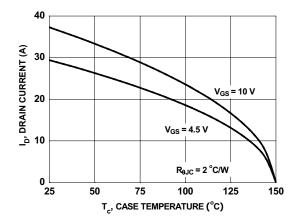


Figure 10. Maximum Continuous Drain Current vs Case Temperature

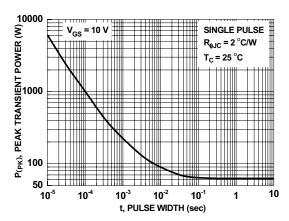


Figure 12. Single Pulse Maximum Power Dissipation

Typical Characteristics T_J = 25 °C unless otherwise noted

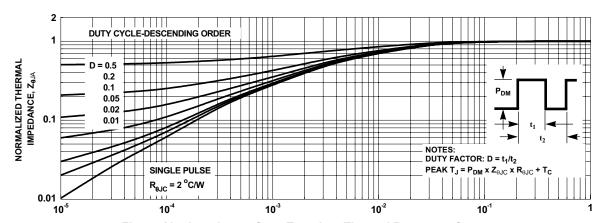


Figure 13. Junction-to-Case Transient Thermal Response Curve





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